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Nota di contenuto	Intro -- Solid-State Power Devices: Circuitry and Characterizations -- Preface -- Table of Contents -- 3rd Quadrant Surge Current SOA of SiC MOSFETs with Different Voltage Class -- Investigation of the Trapping and Detrapping Behavior by the On-State Resistance at Low Off-State Drain Bias in Schottky p-GaN Gate HEMTs -- Junction-Controlled-Diode-Embedded SiC-MOSFET for Improving Third Quadrant and Turn-On Characteristics -- Effect Evaluation and Modeling of p-Type Contact and p-Well Sheet Resistance of SiC MOSFET with Respect to Switching Characteristics -- Ohmic Contact Resistance in SiC Diodes with Ti and NiSi P+ Contacts -- Influence of Material Properties on Ruggedness Evaluation of Package Architectures for SiC Power Devices -- 1.2 kV SiC MOSFET with Low Specific ON-Resistance and High Immunity to Parasitic Turn-On -- Analysis of Electrothermal Imbalance of Hard-Switched Parallel SiC MOSFETs through Infrared Thermography -- Non-Linear Gate Stack Effect on the Short Circuit Performance of a 1.2-kV SiC MOSFET -- A Geometry-Scalable Physically-Based SPICE Compact Model for SiC MPS Diodes Including the Snapback Mechanism -- SiC GAA MOSFET Concept for High Power Electronics Performance Evaluation through Advanced TCAD Simulations -- High-Speed and High-Temperature Switching Operations of a SiC Power MOSFET Using

a SiC CMOS Gate Driver Installed inside a Power Module -- Normally-Off 1200V Silicon Carbide JFET Diode with Low VF -- On the TCAD Modeling of Non-Permanent Gate Current Increase during Short-Circuit Test in SiC MOSFETs -- Study of Parasitic Effects for Accurate Dynamic Characterization of SiC MOSFETs: Comparison between Experimental Measurements and Numerical Simulations -- Analytical Modelling of the Quasi-Static Operation of a Monolithically Integrated 4H-SiC Circuit Breaker Device.

Visualization of P+ JTE Embedded Rings Used for Peripheral Protection of High Voltage Schottky Diodes by the Optical Beam Induced Current (OBIC) Technique -- Design and Characterization of an Optical 4H-SiC Bipolar Junction Transistor -- Temperature-Dependent Evaluation of Commercial 1.2 kV, 40 m 4H-SiC MOSFETs: A Comparative Study between Planar, One-Side Shielded Trench, and Double Trench Gate Structures -- Excellent Avalanche Capability in SiC Power Device with Positively Beveled Mesa Termination -- Frequency Investigation of SiC MOSFETs C-V Curves with Biased Drain -- Experimental Demonstration and Analysis of 3.3kV 4H-SiC Common-Drain Bidirectional Charge-Balanced Power MOSFETs -- Comparison of Si CMOS and SiC CMOS Operational Amplifiers -- Comparative Performance Evaluation of High-Voltage Bidirectional, Conventional and Superjunction Planar DMOSFETs in 4H-SiC -- Comparison of the Surge Current Capabilities of SBD-Embedded and Conventional SiC MOSFETs -- The First Optimisation of a 16 kV 4H-SiC N-Type IGCT -- Influence of Channel Length and Gate Oxide Thickness Variations in 3300 V 4H-SiC VDMOSFET -- Investigation of the Short-Circuit Withstand Time and On-Resistance Trade-Off of 1.2 kV 4H-SiC Power MOSFETs -- Power Cycling Performance of 3.3 kV SiC-MOSFETs and the Impact of the Thermo-Mechanical Stress on Humidity Induced Degradation -- Estimation of Electron Drift Mobility along the c-Axis in 4H-SiC by Using Vertical Schottky Barrier Diodes -- Keyword Index -- Author Index.

Sommario/riassunto

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